Generation of Mid-infrared Frequency Combs on a Silicon Chip

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Comb Generation via Parametric Four-Wave Mixing Oscillation in Microresonators



Octave-Spanning Combs in Near Infrared in Si₃N₄



- Stable, robust, highly compact.
- Modest power requirements (~ 400 mW).

Chip-scale comb source: 10 - 1000 GHz comb spacing $0.8 - 8 \mu m$ wavelength range

Silicon-Based Microresonators for Parametric Comb Generation



- CMOS-compatible material
- Fully monolithic and sealed structures and couplers
- High-Q resonators $\rightarrow Si_3N_4 Q = 7 \times 10^6$ [Luke, et al., *Opt. Express* (2013).]

Si $Q \sim 10^6$ [Lee, et al., (2013).]

- High nonlinearity $\rightarrow n_2 \sim 10-100 \times \text{ silica}$
- Waveguide dispersion can be engineered [Foster, et al., Lipson, Gaeta, *Nature* **441**, 960 (2006).

Tailoring of Dispersion in Si-Based Waveguides





Mid-IR Parametric Frequency Comb in Si₃N₄ Microresonators



- Used improved fabrication process (DSP substrates, anneal mid-deposition, anneal cladding oxide)
- Demonstrated record Q of 1 million at λ = 2.6 μm



Mid-IR Parametric Frequency Comb in Silicon Microresonators



- Q-factor ~10⁶
- Measurement with FTIR OSA
 Bandwidth limited by dynamic range of OSA

^ower (dBm)

- 2608-nm pump
- 750-nm bandwidth
- 125-GHz FSR (100 µm radius)







